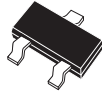


CMPTA96

SURFACE MOUNT
PNP SILICON
EXTREMELY HIGH VOLTAGE
TRANSISTOR



SOT-23 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA96 type is a surface mount epoxy molded PNP silicon planar epitaxial transistors designed for extremely high voltage applications. **Marking Code is C96.**

MAXIMUM RATINGS: (T_A=25°C)

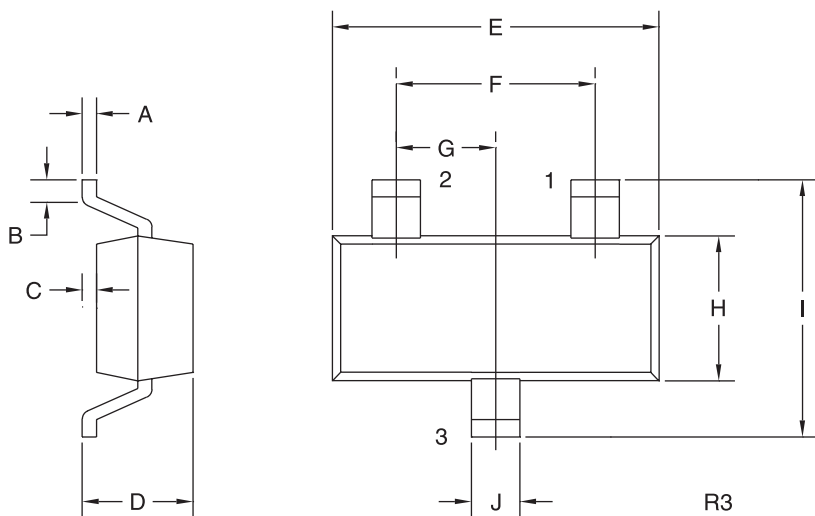
	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	450	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	500	mA
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS:

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =400V			100	nA
I _{EBO}	V _{BE} =4.0V			100	nA
BV _{CBO}	I _C =100μA	450	500		V
BV _{CEO}	I _C =1.0mA	450	490		V
BV _{EBO}	I _E =10μA	6.0	9.7		V
V _{CE(SAT)}	I _C =1.0mA, I _B =0.1mA			0.20	V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA			0.30	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.15	0.50	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA			1.0	V
h _{FE}	V _{CE} =10V, I _C =1.0mA	40			
h _{FE}	V _{CE} =10V, I _C =10mA	50	120	200	
h _{FE}	V _{CE} =10V, I _C =50mA	45			
h _{FE}	V _{CE} =10V, I _C =100mA	25	35		
f _T	V _{CE} =10V, I _C =10mA, f=10MHz	20			MHz
C _{ob}	V _{CB} =20V, I _E =0, f=1.0MHz			7.0	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz			130	

R1 (14-June2001)

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: C96

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (14-June2001)